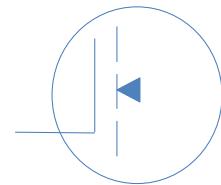


30V N-Ch Power MOSFET

V_{DS}	30	V
$R_{DS(on),typ}$	$V_{GS}=10V$	9.7 m :
$R_{DS(on),typ}$	$V_{GS}=4.5V$	14.5 m :
I_D	12	A



Part Number	Package	Marking
HTS120N03	SOIC-8	TS120N03

Absolute Maximum Ratings at T_j

Parameter	Symbol	Conditions	Value	Unit
Continuous Drain Current (Silicon Limited)	I_D	T_A	12	A
		T_A	10	
Drain to Source Voltage	V_{DS}	-	30	V
Gate to Source Voltage	V_{GS}	-	± 20	V
Pulsed Drain Current	I_{DM}	-	48	A
Avalanche Energy, Single Pulse	E_{AS}	$L=0.3mH, T_C$	7.2	mJ
Power Dissipation	P_D	T_A	3	W
Operating and Storage Temperature	T_J, T_{stg}	-	-55 to 150	

Absolute Maximum Ratings

Parameter	Symbol	Max	Unit
Thermal Resistance Junction-Case	R_{JC}	25	:
Thermal Resistance Junction-Ambient	R_{JA}	50	:

Electrical Characteristics at T_j

X Q O H V V R W K H U Z L V H V S H F L I L H G

			min	typ	max
	$V_{(BR)DSS}$		-	-	3
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS}=0V, V_{DS}=20V, T_j$	-	-	
		$V_{GS}=\pm 20V, V_{DS}=0V$	-		nA
		$V_{GS}=10V, I_D=12A$	-	9.7	
		$V_{GS}=4.5V, I_D=10A$	-	14.5	18



HTS120N03

P-3

Fig 1. Typical Output Characteristics

Figure 2. On-Resistance vs. Gate-Source Voltage

Figure 3. On-Resistance vs. Drain Current and Gate Voltage

) L J X U H 1 R U P D O L] H G 2 Q 5 H V L V W D Q F H Y V - X Q F W L F

) L J X U H 7 \ S L F D O 7 U D Q V I H U & K D U D F W H U Figure 4. Typical Source-Drain Diode Forward Voltage

Figure 7. Typical Gate-Charge vs. Gate-to-Source Voltage

Figure 8. Typical Capacitance vs. Drain-to-Source Voltage

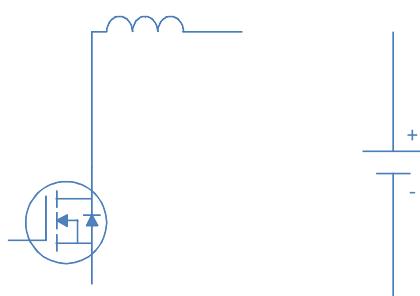
)LJXUH 0D[LPXPDIH 2SHUDWLQJ \$UHDFigure 10. Single Pulse Maximum Power Dissipation

)LJXUH 1RUPDOL]HG 0D[LPXP 7UDQVLHQW 7KHUPDO ,PSHGDQFH -XQFWLR

Inductive switching Test

Gate Charge Test

Uclamped Inductive Switching (UIS) Test



Diode Recovery Test

SOIC-8, 8 leads